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MMBT5401L, SMMBT5401L, NSVMMBT5401L

High Voltage Transistor

PNP Silicon

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	-150	Vdc
Collector–Base Voltage	V_{CBO}	-160	Vdc
Emitter–Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current – Continuous	I_C	-500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

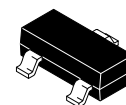
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

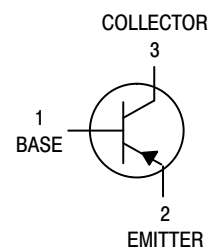


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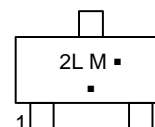
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SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



2L = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBT5401LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
NSVMMBT5401LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBT5401L, SMMBT5401L, NSVMMBT5401L

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = –1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	–150	–	V _{dc}
Collector–Base Breakdown Voltage (I _C = –100 μA _{dc} , I _E = 0)	V _{(BR)CBO}	–160	–	V _{dc}
Emitter–Base Breakdown Voltage (I _E = –10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	–5.0	–	V _{dc}
Collector–Base Cutoff Current (V _{CB} = –120 V _{dc} , I _E = 0) (V _{CB} = –120 V _{dc} , I _E = 0, T _A = 100°C)	I _{CBO}	–	–50	nA _{dc} μA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –5.0 V _{dc}) (I _C = –10 mA _{dc} , V _{CE} = –5.0 V _{dc}) (I _C = –50 mA _{dc} , V _{CE} = –5.0 V _{dc})	h _{FE}	50 60 50	– 240 –	–
Collector–Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{CE(sat)}	– –	–0.2 –0.5	V _{dc}
Base–Emitter Saturation Voltage (I _C = –10 mA _{dc} , I _B = –1.0 mA _{dc}) (I _C = –50 mA _{dc} , I _B = –5.0 mA _{dc})	V _{BE(sat)}	– –	–1.0 –1.0	V _{dc}

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I _C = –10 mA _{dc} , V _{CE} = –10 V _{dc} , f = 100 MHz)	f _T	100	300	MHz
Output Capacitance (V _{CB} = –10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	–	6.0	pF
Small Signal Current Gain (I _C = –1.0 mA _{dc} , V _{CE} = –10 V _{dc} , f = 1.0 kHz)	h _{fe}	40	200	–
Noise Figure (I _C = –200 μA _{dc} , V _{CE} = –5.0 V _{dc} , R _S = 10 Ω, f = 1.0 kHz)	NF	–	8.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

MMBT5401L, SMMBT5401L, NSVMMBT5401L

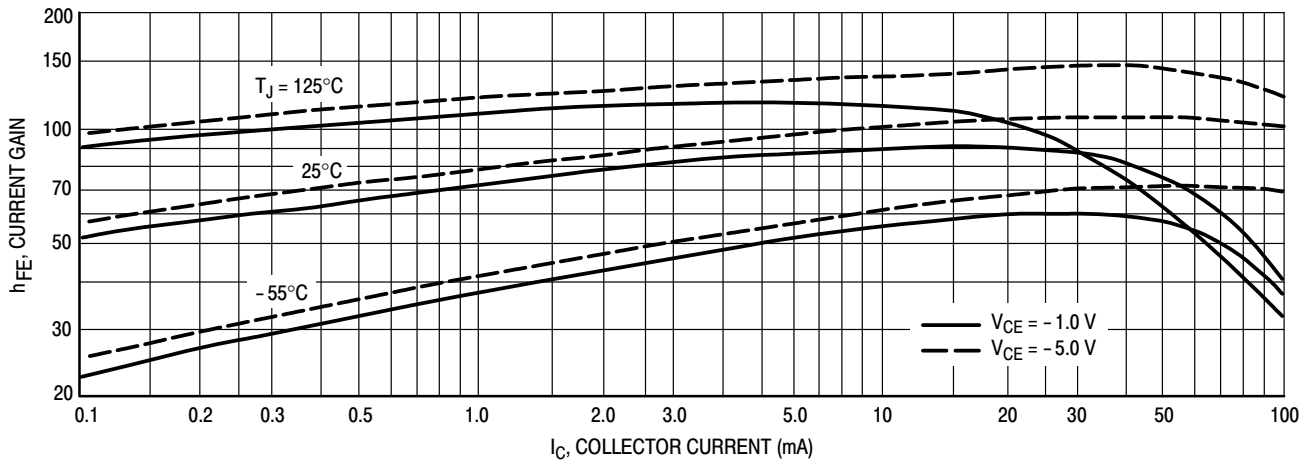


Figure 1. DC Current Gain

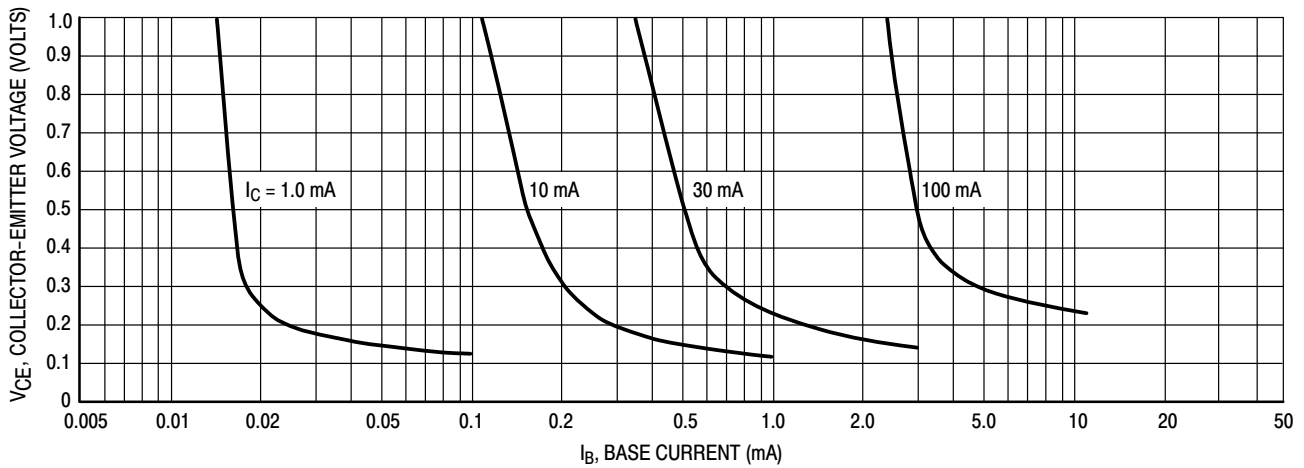


Figure 2. Collector Saturation Region

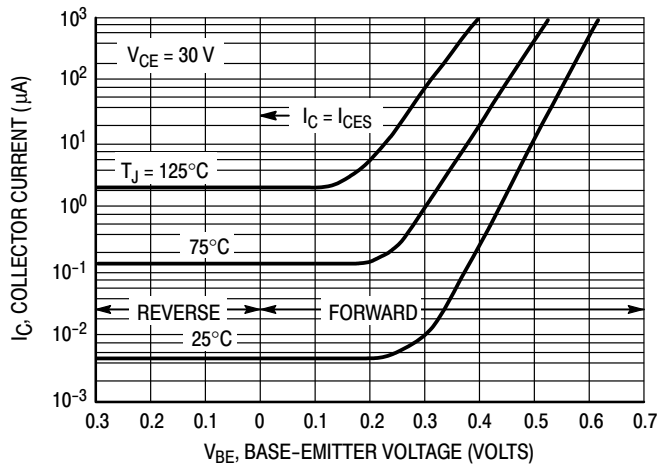


Figure 3. Collector Cut-Off Region

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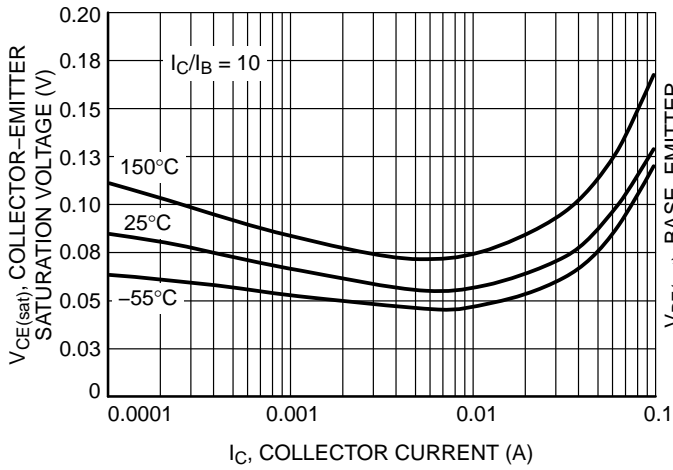


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

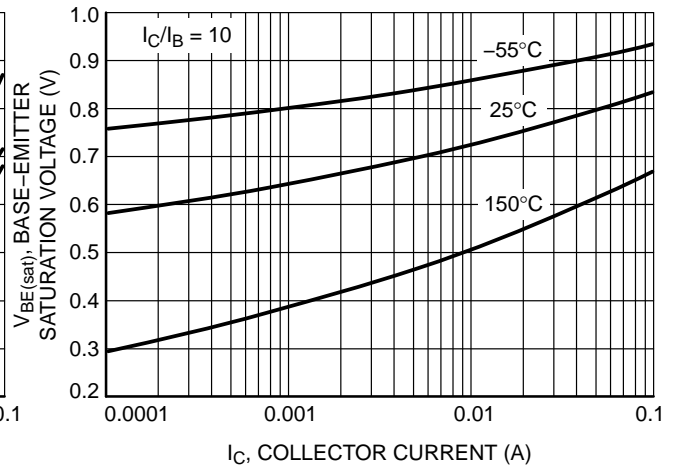


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

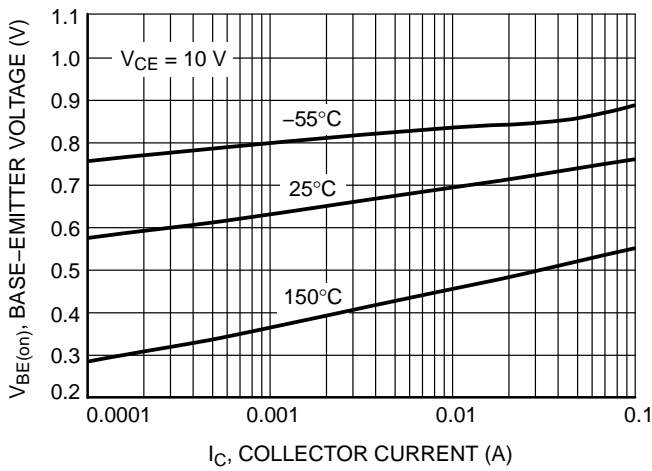


Figure 6. Base-Emitter Voltage vs. Collector Current

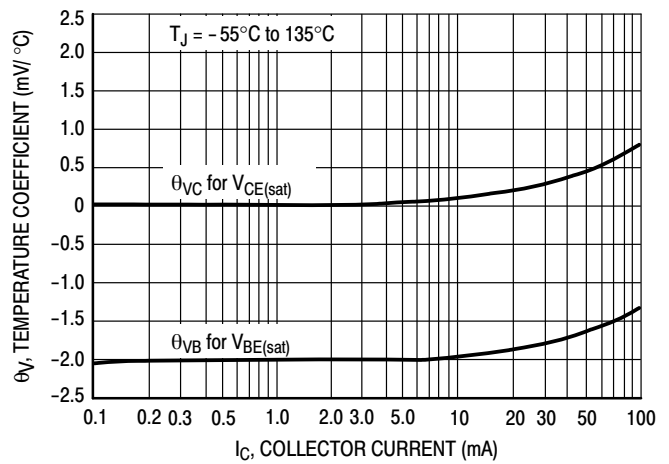


Figure 7. Temperature Coefficients

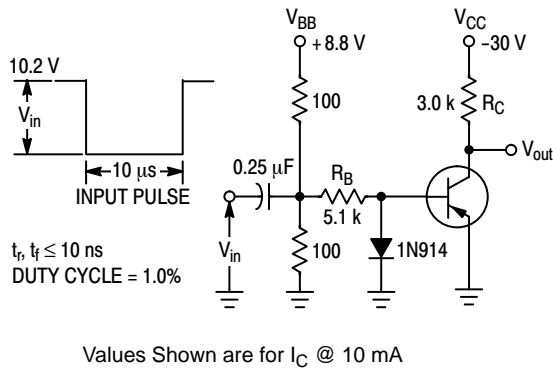


Figure 8. Switching Time Test Circuit

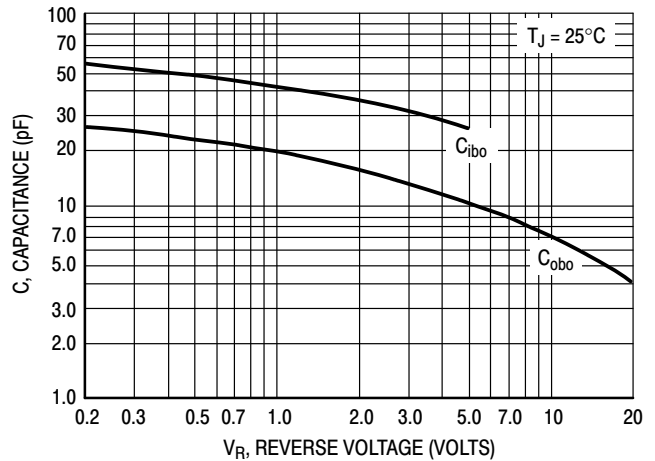


Figure 9. Capacitances

MMBT5401L, SMMBT5401L, NSVMMBT5401L

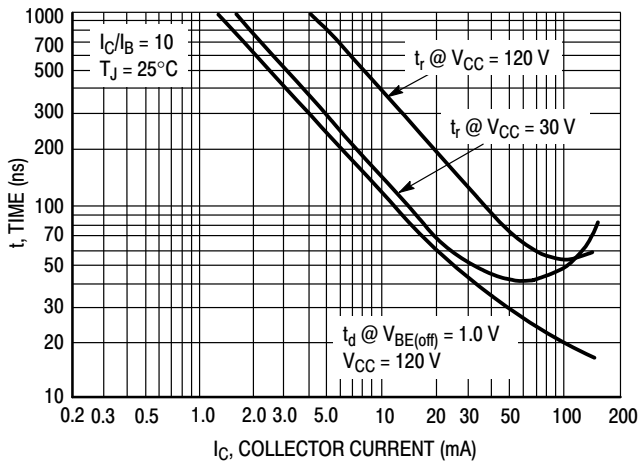


Figure 10. Turn-On Time

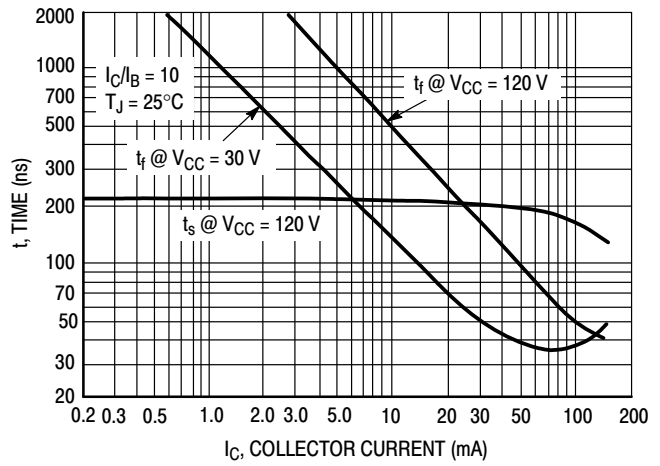


Figure 11. Turn-Off Time

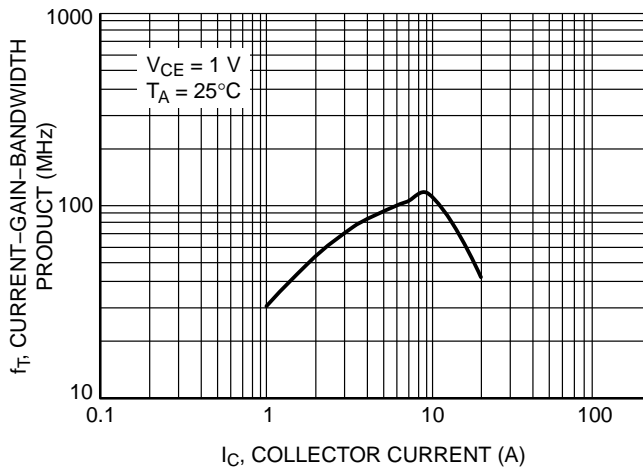


Figure 12. Current Gain Bandwidth Product

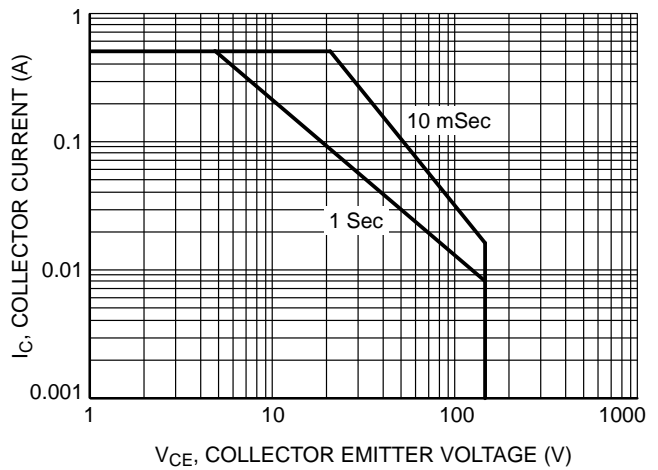


Figure 13. Safe Operating Area

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

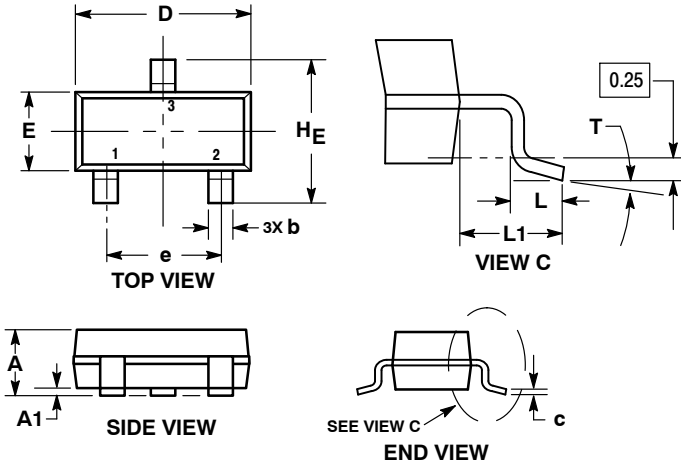
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SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

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